











CDCLVC1102, CDCLVC1103, CDCLVC1104 CDCLVC1106, CDCLVC1108, CDCLVC1110, CDCLVC1112

SCAS895B - MAY 2010-REVISED FEBRUARY 2017

CDCLVC11xx 3.3-V and 2.5-V LVCMOS High-Performance Clock Buffer Family

Features

- High-Performance 1:2, 1:3, 1:4, 1:6, 1:8, 1:10, 1:12 LVCMOS Clock Buffer Family
- Very Low Pin-to-Pin Skew < 50 ps
- Very Low Additive Jitter < 100 fs
- Supply Voltage: 3.3 V or 2.5 V
- $f_{max} = 250 \text{ MHz for } 3.3 \text{ V}$ $f_{max} = 180 \text{ MHz for } 2.5 \text{ V}$
- Operating Temperature Range: -40°C to 85°C
- Available in 8-, 14-, 16-, 20-, 24-Pin TSSOP Package (All Pin-Compatible)

2 Applications

General-Purpose Communication, Industrial, and **Consumer Applications**

3 Description

The CDCLVC11xx is a modular, high-performance, low-skew, general-purpose clock buffer family from Texas Instruments.

The entire family is designed with a modular approach in mind. It is intended to round up TI's series of LVCMOS clock generators.

Seven different fan-out variations, 1:2 to 1:12, are available. All of the devices are pin-compatible to each other for easy handling.

All family members share the same high performing characteristics such as low additive jitter, low skew, and wide operating temperature range.

The CDCLVC11xx supports an asynchronous output enable control (1G) which switches the outputs into a low state when 1G is low.

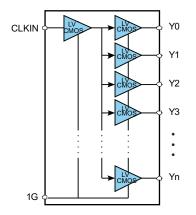
The CDCLVC11xx family operates in a 2.5-V and 3.3-V environment and are characterized for operation from -40°C to 85°C.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
CDCLVC1102				
CDCLVC1103	TSSOP (8)	3.00 mm × 4.40 mm		
CDCLVC1104				
CDCLVC1106	TSSOP (14)	5.00 mm × 4.40 mm		
CDCLVC1108	TSSOP (16)	5.00 mm x 4.40 mm		
CDCLVC1110	TSSOP (20)	6.50 mm × 4.40 mm		
CDCLVC1112	TSSOP (24)	7.80 mm × 4.40 mm		

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.

Functional Block Diagram



CLKIN	1			24	Y1
1G	2	CDCLVC	1102	23	Υ3
Y0	3	CDCLVC	1103	22	VDD
GND	4	CDCLVC	1104	21	Y2
VDD	5			20	GND
Y4	6	CDCLVC	1106	19	Y5
GND	7	CDCLVC	1106	18	VDD
Y6	8	CDCLVC	1108	17	Y7
VDD	9			16	Y8
Y9	10	CDCLVC	1110	15	GND
GND	11			14	Y10
Y11	12	CDCLVC	1112	13	VDD

Page



Table of (Contents
------------	----------

1	Features 1	8.4 Device Functional Modes10
2	Applications 1	9 Application and Implementation 11
3	Description 1	9.1 Application Information11
4	Revision History2	9.2 Typical Application11
5	Pin Configuration and Functions 3	10 Power Supply Recommendations 12
6	Specifications5	10.1 Power Considerations13
•	6.1 Absolute Maximum Ratings 5	11 Layout 14
	6.2 ESD Ratings	11.1 Layout Guidelines14
	6.3 Recommended Operating Conditions	11.2 Layout Example14
	6.4 Thermal Information	12 Device and Documentation Support 15
	6.5 Electrical Characteristics	12.1 Related Links 15
	6.6 Switching Characteristics	12.2 Receiving Notification of Documentation Updates 15
	6.7 Typical Characteristics	12.3 Community Resources
7	Parameter Measurement Information 8	12.4 Trademarks 15
8	Detailed Description 10	12.5 Electrostatic Discharge Caution
•	8.1 Overview	12.6 Glossary
	8.2 Functional Block Diagram	13 Mechanical, Packaging, and Orderable
	8.3 Feature Description	Information

4 Revision History

Cł	hanges from Revision A (October 2014) to Revision B	Page	
•	Changed Packaging name from TTSOP to TSSOP in Device Information Table	1	
•	Changed CDCLVC1110 Y8 pin number from: 10 to: 12	3	
•	Changed CDCLVC1110 Y9 pin number from: — to: 10	3	
•	Moved T _{stg} from ESD Ratings to Absolute Maximum Ratings	5	
•	Added Receiving Notification of Documentation Updates and Community Resources sections	15	

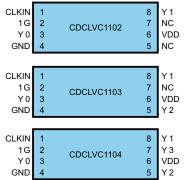
Changes from Original (May 2010) to Revision A

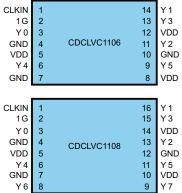


5 Pin Configuration and Functions

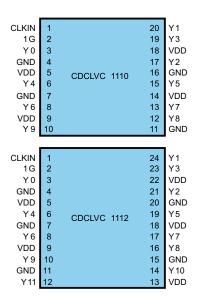
8-, 14-, 16-, 20, 24-Pin TSSOP
Top View

KIN 1 8 Y1 CLKIN 1 14 Y1
1G 2 CDCLVC4403 7 NC 1G 2 13 Y3





PW Package



Pin Functions

					i iii i uii	J.1.J.1.J					
				PIN							
NAME	CDCLVC 1102	CDCLVC 1103	CDCLVC 1104	CDCLVC 1106	CDCLVC 1108	CDCLVC 1110	CDCLVC 1112	TYPE	DESCRIPTION		
LVCMC	LVCMOS CLOCK INPUT										
CLKIN	1	1	1	1	1	1	1	Input	Input Pin		
CLOCK	OUTPUT E	NABLE									
1G	2	2	2	2	2	2	2	Input	Output Enable		
LVCMC	S CLOCK C	UTPUT									
Y0	3	3	3	3	3	3	3				
Y1	8	8	8	14	16	20	24				
Y2	_	5	5	11	13	17	21				
Y3	_	_	7	13	15	19	23				
Y4	_	_	_	6	6	6	6				
Y5	_	_	_	9	11	15	19	Output	LVCMOS output. Unused		
Y6	_	_	_	_	8	8	8	Output	outputs can be left floating.		
Y7	_	_	_	_	9	13	17				
Y8	_	_	_	_	_	12	16				
Y9	_	_	_	_	_	10	10				
Y10	_	_	_	_	_		14				
Y11	_	_	_	_	_		12				
SUPPL	Y VOLTAGE										
						5	5				
				5	5	ວ	9				
V_{DD}	6	6	6			9	13	Power	2.5-V or device supply		
			Ī	8	10	14	18				
				12	14	18	22				
GROUN	ND										

CDCLVC1102, CDCLVC1103, CDCLVC1104 CDCLVC1106, CDCLVC1108, CDCLVC1110, CDCLVC1112





www.ti.com

Pin Functions (continued)

				PIN					DESCRIPTION			
NAME	CDCLVC 1102	CDCLVC 1103	CDCLVC 1104	CDCLVC 1106	CDCLVC 1108	CDCLVC 1110	CDCLVC 1112	TYPE				
						4	4					
				4	4	4	7					
GND	4	4	4			7	11	GND	GND	GND	GND	Device ground
				7	7	11	15					
				10	12	16	20	1				



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	-0.5	4.6	V
V _{IN}	Input voltage ⁽²⁾	-0.5	V _{DD} + 0.5	V
Vo	Output voltage ⁽²⁾	-0.5	V _{DD} + 0.5	V
I _{IN}	Input current	-20	20	mA
Io	Continuous output current	-50	50	mA
T_J	Maximum junction temperature		125	°C
T _{stg}	Storage temperature	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V	V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
V(ESD)		Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
.,	0	3.3-V supply	3.0	3.3	3.6	
V_{DD}	Supply voltage	2.5-V supply	2.3	2.5	2.7	V
M. Lauri Invalidant valtana	V _{DD} = 3.0 V to 3.6 V			V _{DD} /2 – 600	\/	
V_{IL}	L Low-level input voltage	V _{DD} = 2.3 V to 2.7 V			V _{DD} /2 - 400	mV
.,	LPale Level Secret college	V _{DD} = 3.0 V to 3.6 V	V _{DD} /2 + 600			
V_{IH}	High-level input voltage	V _{DD} = 2.3 V to 2.7 V	V _{DD} /2 + 400			mV
V_{th}	Input threshold voltage	V _{DD} = 2.3 V to 3.6 V		V _{DD} /2		mV
t _r / t _f	Input slew rate		1		4	V/ns
	Minimum pulse width at	V _{DD} = 3.0 V to 3.6 V	1.8			
t _w	CLKIN	V _{DD} = 2.3 V to 2.7 V	2.75			ns
,	LVCMOS clock Input	V _{DD} = 3.0 V to 3.6 V	DC		250	N.41.1-
f _{CLK}	Frequency	V _{DD} = 2.3 V to 2.7 V	DC		180	MHz
T _A	Operating free-air tempera	ture	-40		85	°C

⁽²⁾ This value is limited to 4.6 V maximum.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		CDCI VC4404		CDCLVC11010	CDCLVC1112	UNIT		
		PW (TSSOP)						
		8 PINS	14 PINS	16 PINS	20 PINS	24 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance (2)	149.4	112.6	108.4	83.0	87.9	°C/W	
R _{θJC(top)}	Junction-to-case(top) thermal resistance (3)	69.4	48.0	33.6	32.3	26.5	°C/W	

For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report.

The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.

The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDECstandard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

6.5 Electrical Characteristics

Over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
OVER	RALL PARAMETERS FOR ALL V	ERSIONS			•	
	Static device current (2)	$1G = V_{DD}$; CLKIN = 0 V or V_{DD} ; I_{O} = 0 mA; V_{DD} = 3.6 V		6	10	mA
I _{DD}	Static device current	$1G = V_{DD}$; CLKIN = 0 V or V_{DD} ; $I_O = 0$ mA; $V_{DD} = 2.7$ V		3	6	
I_{PD}	Power-down current	$1G = 0 \text{ V}$; CLKIN = 0 V or V_{DD} ; $I_{O} = 0 \text{ mA}$; $V_{DD} = 3.6 \text{ V}$ or 2.7 V			60	μΑ
C	Power dissipation capacitance	$V_{DD} = 3.3 \text{ V; } f = 10 \text{ MHz}$		6		pF
C _{PD}	per output (3)	V _{DD} = 2.5 V; f = 10 MHz		4.5		
	Input leakage current at 1G	V 0 V 0 V V 2 6 V 0 2 7 V	8		8	
l _l	Input leakage current at CLKIN	$V_1 = 0 \text{ V or } V_{DD}, V_{DD} = 3.6 \text{ V or } 2.7 \text{ V}$	25		25	μA
D	Output impedance	$V_{DD} = 3.3 \text{ V}$		45		Ω
R _{OUT}	Output Impedance	V _{DD} = 2.5 V		60		
ı	Output fraguesia	$V_{DD} = 3 \text{ V to } 3.6 \text{ V}$	DC		250	MHz
f _{OUT}	Output frequency	$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$	DC		180	
OUTP	PUT PARAMETERS FOR V _{DD} = 3	.3 V ± 0.3 V				
		$V_{DD} = 3 \text{ V}, I_{OH} = -0.1 \text{ mA}$	2.9			
V_{OH}	High-level output voltage	$V_{DD} = 3 \text{ V}, I_{OH} = -8 \text{ mA}$	2.5			V
		$V_{DD} = 3 \text{ V}, I_{OH} = -12 \text{ mA}$	2.2			
		$V_{DD} = 3 \text{ V}, I_{OL} = 0.1 \text{ mA}$			0.1	
V_{OL}	Low-level output voltage	$V_{DD} = 3 \text{ V}, I_{OL} = 8 \text{ mA}$			0.5	V
		$V_{DD} = 3 \text{ V}, I_{OL} = 12 \text{ mA}$			8.0	
OUTP	PUT PARAMETERS FOR V _{DD} = 2	.5 V ± 0.2 V				
.,	I limb lavel autout valtage	$V_{DD} = 2.3 \text{ V}, I_{OH} = -0.1 \text{ mA}$	2.2			V
V _{OH}	High-level output voltage	$V_{DD} = 2.3 \text{ V}, I_{OH} = -8 \text{ mA}$	1.7			٧
\/	Low lovel output voltage	V _{DD} = 2.3 V, I _{OL} = 0.1 mA			0.1	V
V_{OL}	Low-level output voltage	V _{DD} = 2.3 V, I _{OL} = 8 mA			0.5	V

⁽¹⁾ All typical values are at respective nominal V_{DD} . For switching characteristics, outputs are terminated to 50 Ω to $V_{DD}/2$ (see Figure 3).

For dynamic I_{DD} over frequency see and Figure 1.

 $P_{\text{tot}} = P_{\text{stat}} + P_{\text{dyn}} + P_{\text{Cload}} [W]$ $P_{\text{stat}} = V_{\text{DD}} \times I_{\text{DD}} [W]$ $P_{\text{dyn}} = C_{\text{PD}} \times V_{\text{DD2}} \times f [W]$

 $P_{Cload} = C_{load} \times V_{DD} 2 \times f \times n [W]$

n = Number of switching output pins

This is the formula for the power dissipation calculation (see and the *Power Considerations* section).



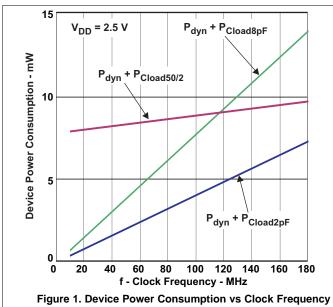
6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
OUTPUT P	ARAMETERS FOR V _{DD} = 3.3	3 V ± 0.3 V			
t _{PLH} , t _{PHL}	Propagation delay	CLKIN to Yn	0.8	2.0	ns
t _{sk(o)}	Output skew	Equal load of each output		50	ps
t _r /t _f	Rise and fall time	20%–80% (V _{OH} - V _{OL})	0.3	0.8	ns
t _{DIS}	Output disable time	1G to Yn		6	ns
t _{EN}	Output enable time	1G to Yn		6	ns
t _{sk(p)}	Pulse skew ; $t_{PLH(Yn)} - t_{PHL(Yn)}$ (1)	To be measured with input duty cycle of 50%		180	ps
t _{sk(pp)}	Part-to-part skew	Under equal operating conditions for two parts		0.5	ns
t _{jitter}	Additive jitter rms ⁽²⁾	12 kHz to 20 MHz, f _{OUT} = 250 MHz		100	fs
OUTPUT P	ARAMETERS FOR V _{DD} = 2.5	5 V ± 0.2 V			
t _{PLH} , t _{PHL}	Propagation delay	CLKIN to Yn	1	2.6	ns
t _{sk(o)}	Output skew	Equal load of each output		50	ps
t _r /t _f	Rise and fall time	20%-80% reference point	0.3	1.2	ns
t _{DIS}	Output disable time	1G to Yn		10	ns
t _{EN}	Output enable time	1G to Yn		10	ns
t _{sk(p)}	Pulse skew ; $t_{PLH(Yn)} - t_{PHL(Yn)}$ (1)	To be measured with input duty cycle of 50%		220	ps
t _{sk(pp)}	Part-to-part skew	Under equal operating conditions for two parts		1.2	ns
t _{jitter}	Additive jitter rms ⁽²⁾	12 kHz to 20 MHz, f _{OUT} = 180 MHz		350	fs

 $t_{sk(p)}$ depends on output rise- and fall-time (t_r/t_f) . The output duty-cycle can be calculated: odc = $(t_{w(OUT)} \pm t_{sk(p)})/t_{period}$; $t_{w(OUT)}$ is pulsewidth of output waveform and tperiod is $1/t_{OUT}$. Parameter is specified by characterization. Not tested in production.

6.7 Typical Characteristics



(Load 50 Ω into V_{DD}/2; 2 pF, 8 pF; Per Output)

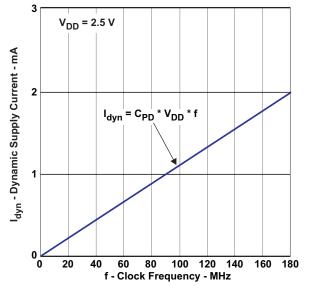


Figure 2. Dynamic Supply Current vs Clock Frequency (C_{PD} = 4.5 pF, No Load; Per Output)



7 Parameter Measurement Information

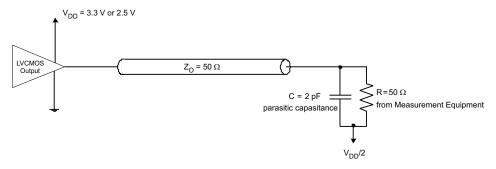


Figure 3. Test Load Circuit

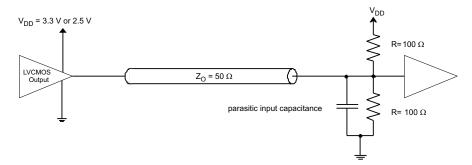


Figure 4. Application Load With 50- Ω Line Termination

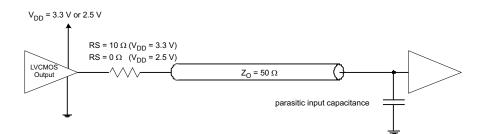


Figure 5. Application Load With Series Line Termination

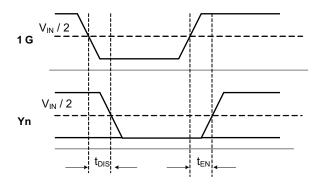


Figure 6. t_{DIS} and t_{EN} for Disable Low

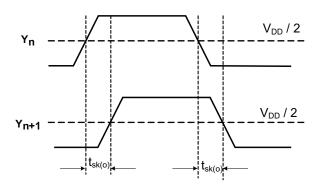


Figure 7. Output Skew t_{sk(o)}



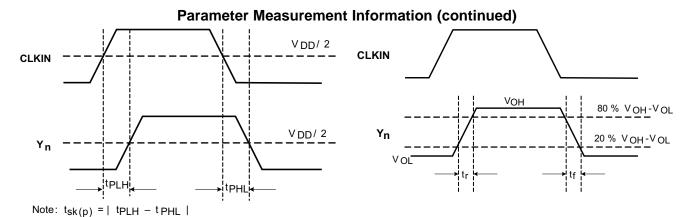


Figure 8. Pulse Skew $t_{\text{sk(p)}}$ and Propagation Delay $t_{\text{PLH}}/t_{\text{PHL}}$

Figure 9. Rise/Fall Times t_r/t_f

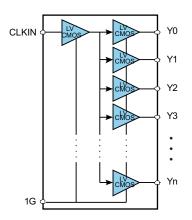


8 Detailed Description

8.1 Overview

The CDCLVC11xx family of devices is a low-jitter and low-skew LVCMOS fan-out buffer solution. For best signal integrity, it is important to match the characteristic impedance of the CDCLVC11xx's output driver with that of the transmission line. Figure 5 and Figure 6 show the proper configuration per configuration for both $V_{DD} = 3.3 \text{ V}$ and $V_{DD} = 2.5 \text{ V}$. TI recommends placing the series resistor close to the driver to minimize signal reflection.

8.2 Functional Block Diagram



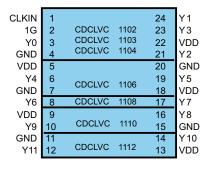


Table 1. Output Logic Table

INP	OUTPUTS	
CLKIN	1G	Yn
X	L	L
L	Н	L
Н	Н	Н

8.3 Feature Description

The outputs of the CDCLVC11xx can be disabled by driving the asynchronous output enable pin (1G) low. Unused output can be left floating to reduce overall system component cost. All supply and ground pins must be connected to V_{DD} and GND, respectively.

8.4 Device Functional Modes

The CDCLVC11xx operates from supplies between 2.5 V and 3.3 V.



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The CDCLVC11xx family is a low additive jitter LVCMOS buffer solution that can operate up to 250 MHz at and 180 MHz at $V_{DD} = 2.5$ V. Low output skew as well as the ability for asynchronous output enable is featured to simultaneously enable or disable buffered clock outputs as necessary in the application.

9.2 Typical Application

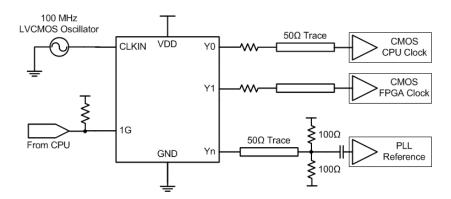


Figure 10. Example System Configuration

9.2.1 Design Requirements

The CDCLVC11xx shown in Figure 10 is configured to fan out a 100-MHz signal from a local LVCMOS oscillator. The CPU is configured to control the output state through 1G.

The configuration example is driving three LVCMOS receivers in a backplane application with the following properties:

- The CPU clock can accept a full swing DC-coupled LVCMOS signal. A series resistor is placed near the CDCLVC11xx to closely match the characteristic impedance of the trace to minimize reflections.
- The FPGA clock is similarly DC-coupled with an appropriate series resistor placed near the CDCLVC11xx.
- The PLL in this example can accept a lower amplitude signal, so a Thevenin's equivalent termination is used.
 The PLL receiver features internal biasing, so AC coupling can be used when common-mode voltage is mismatched.

9.2.2 Detailed Design Procedure

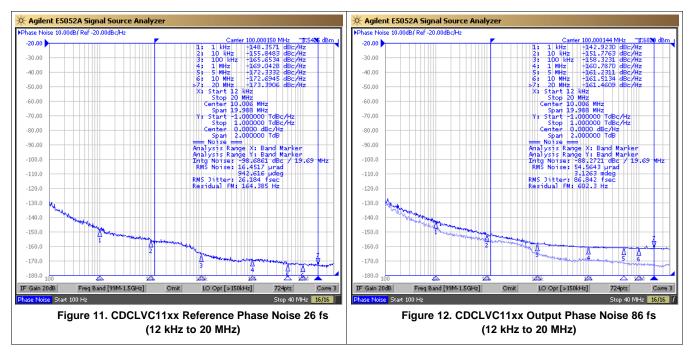
Refer to Figure 5 and the *Electrical Characteristics* table to determine the appropriate series resistance needed for matching the output impedance of the CDCLVC11xx to that of the characteristic impedance of the transmission line.

Unused outputs can be left floating. See the *Power Supply Recommendations* section for recommended filtering techniques.



Typical Application (continued)

9.2.3 Application Curves



The low additive jitter of the CDCLVC11xx can be shown in the previous application example. The low-noise 100-MHz XO with 26-fs RMS jitter drives the CDCLVC11xx, resulting in 86-fs RMS jitter when integrated from 12 kHz to 20 MHz. The resultant additive jitter is a low 82-fs RMS for this configuration.

10 Power Supply Recommendations

High-performance clock buffers are sensitive to noise on the power supply, which can dramatically increase the additive jitter of the buffer. Thus, it is essential to reduce noise from the system power supply, especially when the jitter and phase noise is critical to applications.

Filter capacitors are used to eliminate the low-frequency noise from the power supply, where the bypass capacitors provide the very low impedance path for high-frequency noise and guards the power supply system against induced fluctuations. These bypass capacitors also provide instantaneous current surges as required by the device and should have low equivalent series resistance (ESR). To properly use the bypass capacitors, they must be placed very close to the power-supply terminals and laid out with short loops to minimize inductance. TI recommends adding as many high-frequency (for example, 0.1 μF) bypass capacitors, as there are supply terminals in the package. TI recommends, but does not require, inserting a ferrite bead between the board power supply and the chip power supply that isolates the high-frequency switching noises generated by the clock buffer; these beads prevent the switching noise from leaking into the board supply. It is imperative to choose an appropriate ferrite bead with very low DC resistance to provide adequate isolation between the board supply and the chip supply, as well as to maintain a voltage at the supply terminals that is greater than the minimum voltage required for proper operation.



Figure 13 shows this recommended power supply decoupling method.

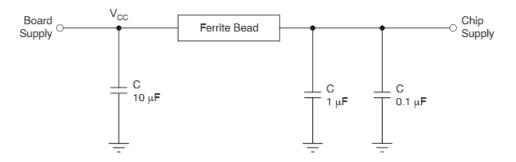


Figure 13. Power Supply Decoupling

10.1 Power Considerations

The following power consideration refers to the device-consumed power consumption only. The device power consumption is the sum of static power and dynamic power. The dynamic power usage consists of two components:

- · Power used by the device as it switches states.
- Power required to charge any output load.

The output load can be capacitive only or capacitive and resistive. The following formula and the power graphs in and Figure 1 can be used to obtain the power consumption of the device:

$$P_{dev} = P_{stat} + n (P_{dyn} + P_{Cload})$$

 $P_{stat} = V_{DD} \times I_{DD}$
 $P_{dyn} + P_{Cload} = see and Figure 1$

where:

```
V_{DD} = Supply voltage ( or 2.5 V) I_{DD} = Static device current (typical 6 mA for V_{DD} = 3.3 V; typical 3 mA for V_{DD} = 2.5 V) I_{DD} = Number of switching output pins
```

Example for device power consumption for CDCLVC1104: four outputs are switching, f = 120 MHz, V_{DD} = 3.3 V, and C_{load} = 2 pF per output:

$$P_{dev} = P_{stat} + n (P_{dyn} + P_{Cload}) = 19.8 \text{ mW} + 40 \text{ mW} = 59.8 \text{ mW}$$

 $P_{stat} = V_{DD} \times I_{DD} = 6 \text{ mA} \times 3.3 \text{ V} = 19.8 \text{ mW}$
 $n (P_{dyn} + P_{Cload}) = 4 \times 10 \text{ mW} = 40 \text{ mW}$

NOTE

For dimensioning the power supply, the total power consumption must be considered. The total power consumption is the sum of the device power consumption and the power consumption of the load.



11 Layout

11.1 Layout Guidelines

Figure 14 shows a conceptual layout detailing recommended placement of power supply bypass capacitors. For component side mounting, use 0402 body size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low-impedance connection to the ground plane.

11.2 Layout Example

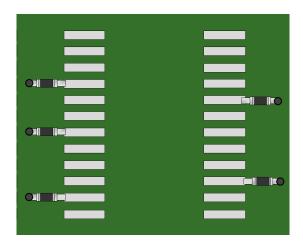


Figure 14. PCB Conceptual Layout



12 Device and Documentation Support

12.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 2. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
CDCLVC1102	Click here	Click here	Click here	Click here	Click here
CDCLVC1103	Click here	Click here	Click here	Click here	Click here
CDCLVC1104	Click here	Click here	Click here	Click here	Click here
CDCLVC1106	Click here	Click here	Click here	Click here	Click here
CDCLVC1108	Click here	Click here	Click here	Click here	Click here
CDCLVC1110	Click here	Click here	Click here	Click here	Click here
CDCLVC1112	Click here	Click here	Click here	Click here	Click here

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





8-Oct-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CDCLVC1102PW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C2	Samples
CDCLVC1102PWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C2	Samples
CDCLVC1103PW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C3	Samples
CDCLVC1103PWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C3	Samples
CDCLVC1104PW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C4	Samples
CDCLVC1104PWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C4	Samples
CDCLVC1106PW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C6	Samples
CDCLVC1106PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C6	Samples
CDCLVC1108PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C8	Samples
CDCLVC1108PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C8	Samples
CDCLVC1110PW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CA	Samples
CDCLVC1110PWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CA	Samples
CDCLVC1112PW	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CC	Samples
CDCLVC1112PWR	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CC	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.



PACKAGE OPTION ADDENDUM

8-Oct-2015

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 21-Apr-2016

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCLVC1102PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
CDCLVC1103PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
CDCLVC1104PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
CDCLVC1106PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CDCLVC1108PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CDCLVC1110PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
CDCLVC1112PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

www.ti.com 21-Apr-2016



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CDCLVC1102PWR	TSSOP	PW	8	2000	367.0	367.0	35.0
CDCLVC1103PWR	TSSOP	PW	8	2000	367.0	367.0	35.0
CDCLVC1104PWR	TSSOP	PW	8	2000	367.0	367.0	35.0
CDCLVC1106PWR	TSSOP	PW	14	2000	367.0	367.0	35.0
CDCLVC1108PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
CDCLVC1110PWR	TSSOP	PW	20	2000	367.0	367.0	38.0
CDCLVC1112PWR	TSSOP	PW	24	2000	367.0	367.0	38.0





- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153







- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2019, Texas Instruments Incorporated